

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07354 DT-33-21

2SB754

SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

Unit in mm

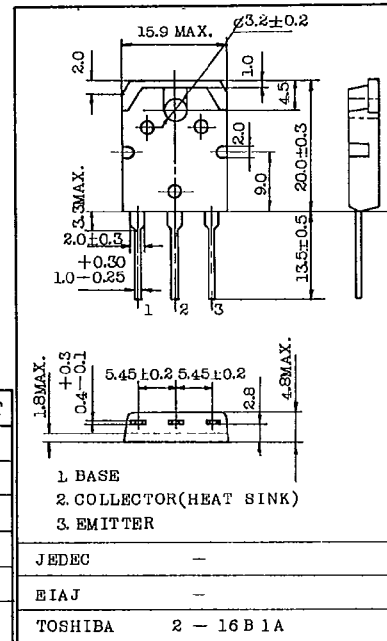
HIGH CURRENT SWITCHING APPLICATIONS.
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- High Collector Current : $I_C = -7A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.4V$ (Max.) at $I_C = -4A$
- High Power Dissipation : $P_C = 60W$ at $T_c = 25^\circ C$
- Complementary to 2SD844.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CE0}	-50	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-7	A
Emitter Current	I _E	7	A
Collector Power Dissipation	P _C	T _a =25°C	2.5
		T _c =25°C	60
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



Weight : 4.6g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = -50V, I _E = 0	-	-	-10	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} = -5V, I _C = 0	-	-	-10	μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = -50mA, I _B = 0	-50	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = -10mA, I _C = 0	-5	-	-	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} = -1V, I _C = -1A	70	-	240	
	h _{FE} (2)	V _{CE} = -1V, I _C = -4A	30	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -4A, I _B = -0.4A	-	-0.2	-0.4	V
Base-Emitter Voltage	V _{BE}	V _{CE} = -1V, I _C = -4A	-	-0.9	-1.2	V
Transition Frequency	f _T	V _{CE} = -5V, I _C = -1A	-	10	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	-	300	-	pF

Note : h_{FE}(1) Classification O : 70~140 Y : 120~240

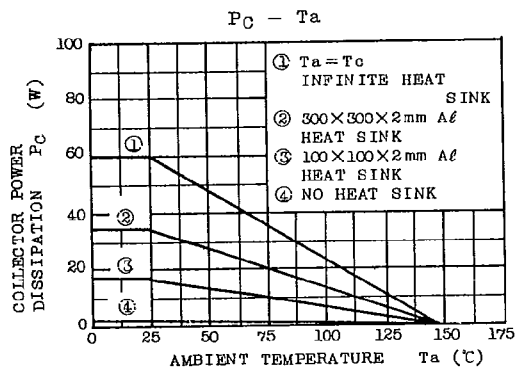
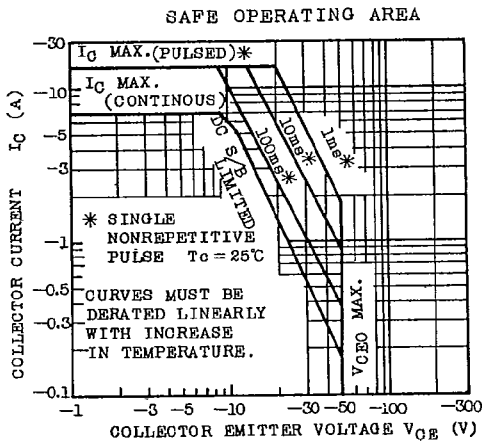
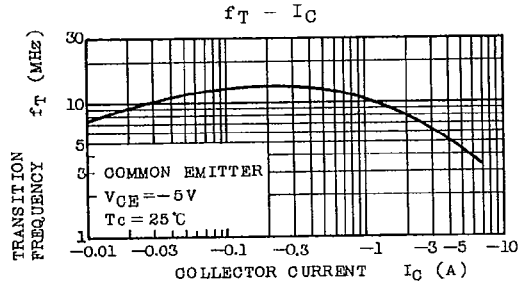
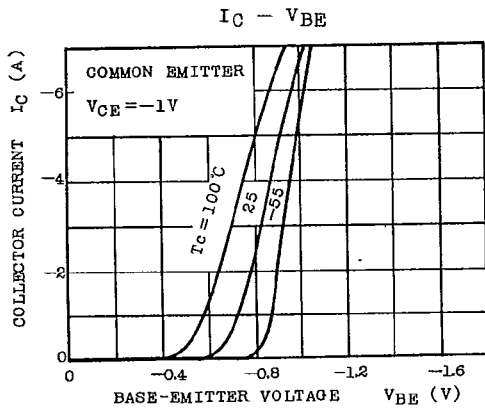
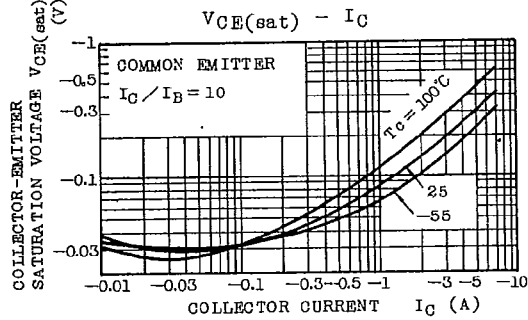
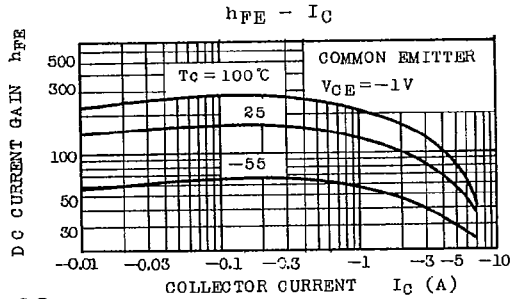
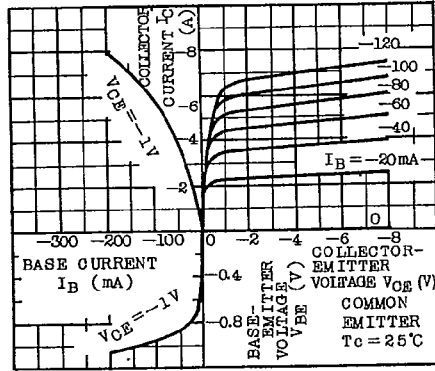
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STATIC CHARACTERISTICS



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